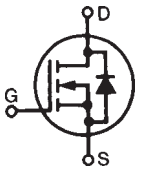
IXYS

PolarHT™ Power MOSFET

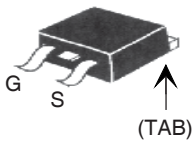
IXTA16N50P
IXTP16N50P
IXTQ16N50P

V_{DSS} = 500V
I_{D25} = 16A
$R_{DS(on)}$ ≤ 400mΩ

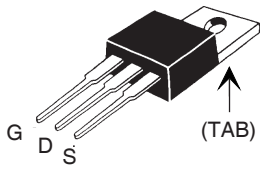
N-Channel Enhancement Mode
Avalanche Rated



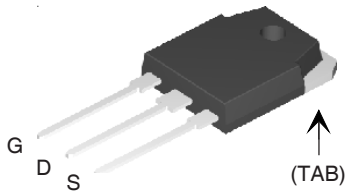
TO-263 (IXTA)



TO-220 (IXTP)



TO-3P (IXTQ)



G = Gate D = Drain
S = Source TAB = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	500	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	500	V
V_{GSS}	Continuous	±30	V
V_{GSM}	Transient	±40	V
I_{D25}	T_C = 25°C	16	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	35	A
I_A	T_C = 25°C	16	A
E_{AS}	T_C = 25°C	750	mJ
dV/dt	$I_S \le I_{DM}$, $V_{DD} \le V_{DSS}$, $T_J \le 150°C$	10	V/ns
P_D	T_C = 25°C	300	W
T_J		- 55 ... +150	°C
T_{JM}		150	°C
T_{stg}		- 55 ... +150	°C
T_L	1.6mm (0.062 in.) from Case for 10s	300	°C
T_{SOLD}	Plastic Body for 10s	260	°C
M_d	Mounting Torque (TO-3P,TO-220)	1.13/10	Nm/lb.in.
Weight	TO-263	2.5	g
	TO-220	3.0	g
	TO-3P	5.5	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 250μA	500			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 250μA	3.0		5.5	V
I_{GSS}	V_{GS} = ±30V, V_{DS} = 0V			±100	nA
I_{DSS}	$V_{DS} = V_{DSS}$, V_{GS} = 0V			5	μA
	T_J = 125°C			50	μA
$R_{DS(on)}$	V_{GS} = 10V, $I_D = 0.5 \bullet I_{D25}$, Note 1			400	mΩ

Features

- International Standard Packages
- Avalanche Rated
- Fast Intrinsic Diode
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switched-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- Laser Drivers
- AC and DC Motor Drives
- Robotics and Servo Controls

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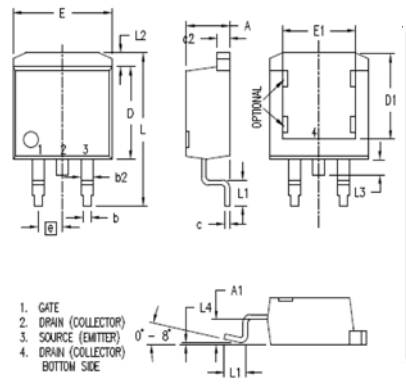
Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS} = 20V, I_D = 0.5 • I_{D25}, Note 1	9	16		S
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		2480		pF
C_{oss}			237		pF
C_{rss}			18		pF
$t_{d(on)}$	**Resistive Switching Times**		23		ns
t_r	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		25		ns
$t_{d(off)}$	R_G = 10Ω (External)		70		ns
t_f			22		ns
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		43		nC
Q_{gs}			15		nC
Q_{gd}			12		nC
R_{thJC}				0.42	°C/W
R_{thCS}	(TO-3P)		0.25		°C/W
	(TO-220)		0.50		°C/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0V			16	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			64	A
V_{SD}	I_F = 16A, V_{GS} = 0V, Note 1			1.5	V
t_{rr}	I_F = 16A, -di/dt = 100A/μs V_R = 100V, V_{GS} = 0V		400		ns

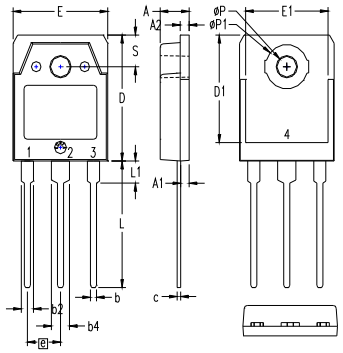
Note 1: Pulse Test, t ≤ 300μs; Duty Cycle, d ≤ 2%.

TO-263 (IXTA) Outline



SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

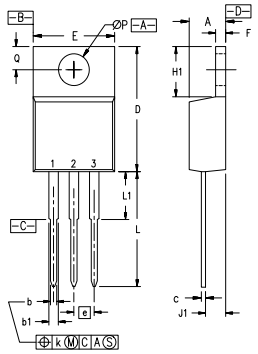
TO-3P (IXTQ) Outline



1 – GATE
2 – DRAIN (COLLECTOR)
3 – SOURCE (EMITTER)
4 – DRAIN (COLLECTOR)

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.185	.193	4.70	4.90
A1	.051	.059	1.30	1.50
A2	.057	.065	1.45	1.65
b	.035	.045	0.90	1.15
b2	.075	.087	1.90	2.20
b4	.114	.126	2.90	3.20
c	.022	.031	0.55	0.80
D	.780	.799	19.80	20.30
D1	.665	.677	16.90	17.20
E	.610	.622	15.50	15.80
E1	.531	.539	13.50	13.70
e	.215 BSC		5.45 BSC	
L	.779	.795	19.80	20.20
L1	.134	.142	3.40	3.60
øP	.126	.134	3.20	3.40
øP1	.272	.280	6.90	7.10
S	.193	.201	4.90	5.10

TO-220 (IXTP) Outline



Pins: 1 - Gate 2 - Drain
3 - Source 4 - Drain

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

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IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,850,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405 B2 6,710,463 6,727,585 6,759,692 6,771,478 B2 7,005,734 B2 7,063,975 B2 7,071,537 7,157,338B2

Fig. 1. Output Characteristics @ 25ºC

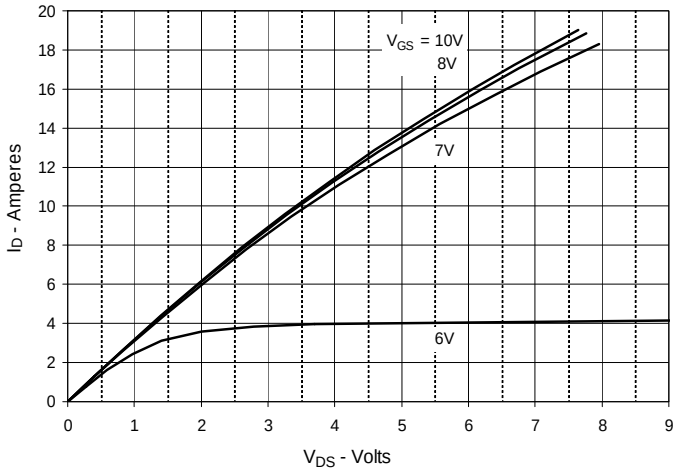


Fig. 2. Output Characteristics @ 125ºC

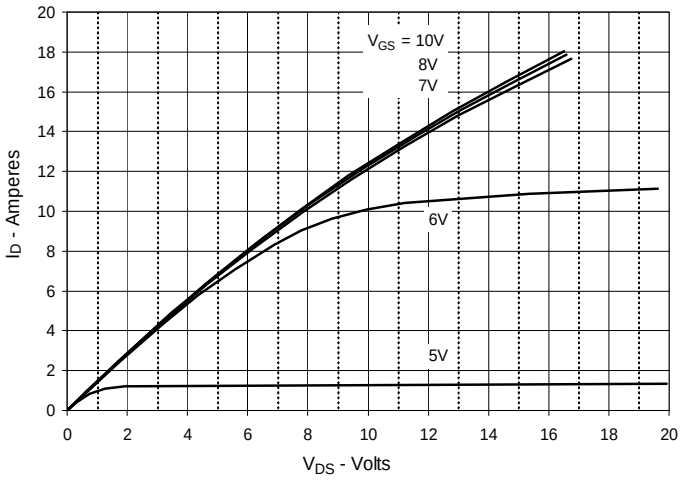


Fig. 3. $R_{DS(on)}$ Normalized to I_D = 8A Value vs. Junction Temperature

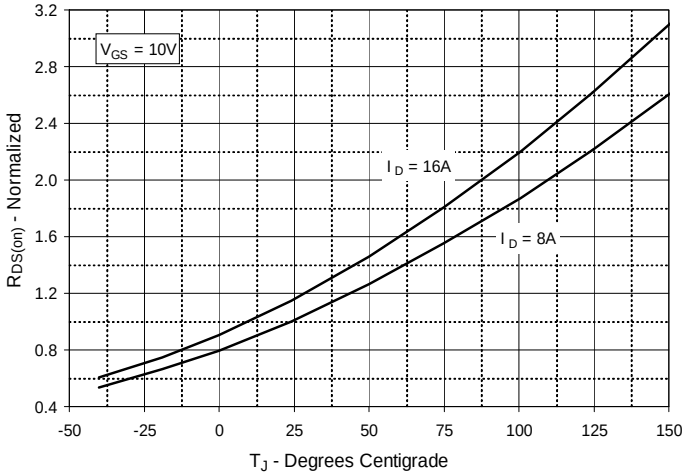


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 8A Value vs. Drain Current

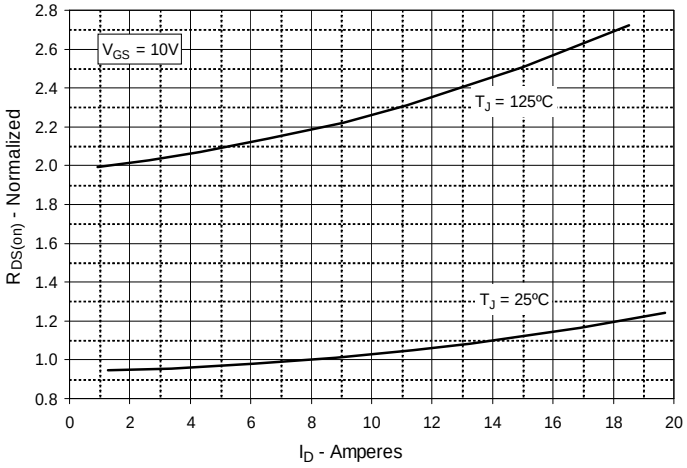


Fig. 5. Maximum Drain Current vs. Case Temperature

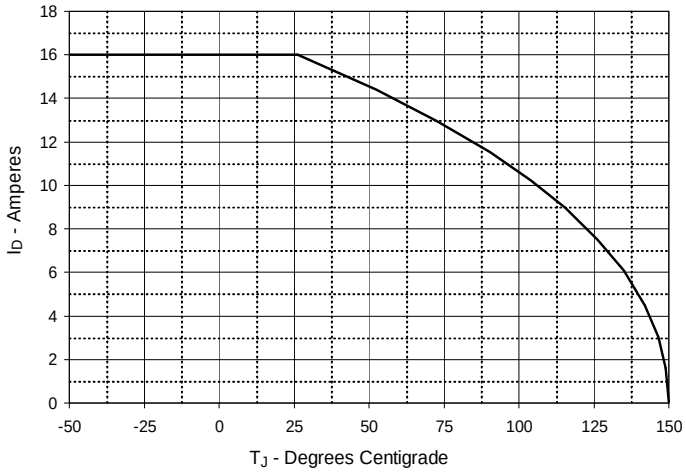
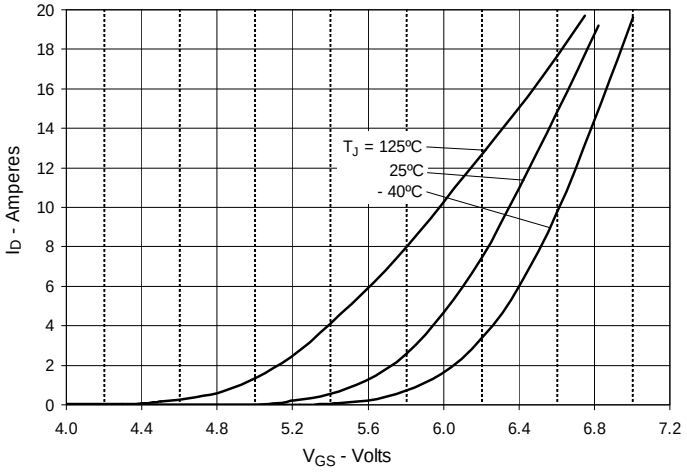


Fig. 6. Input Admittance



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Fig. 7. Transconductance

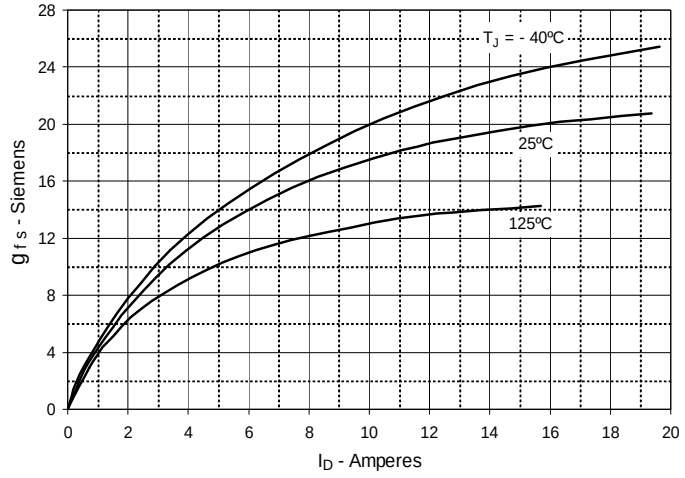


Fig. 8. Forward Voltage Drop of Intrinsic Diode

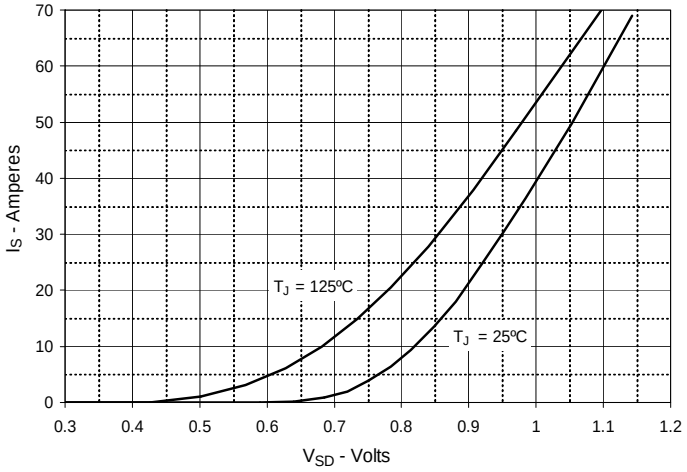


Fig. 9. Gate Charge

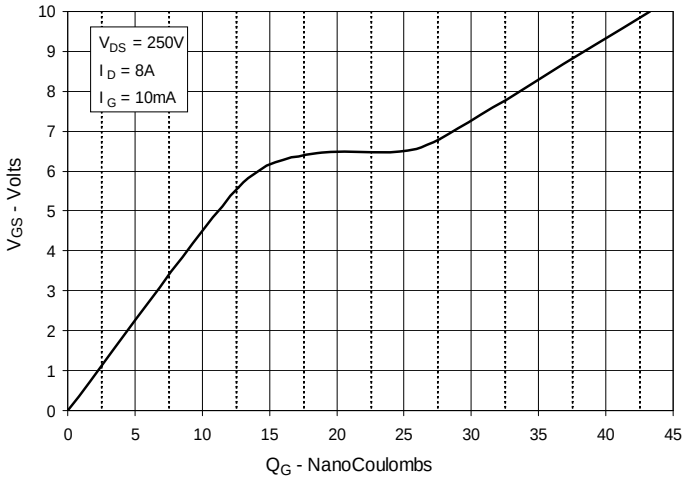


Fig. 10. Capacitance

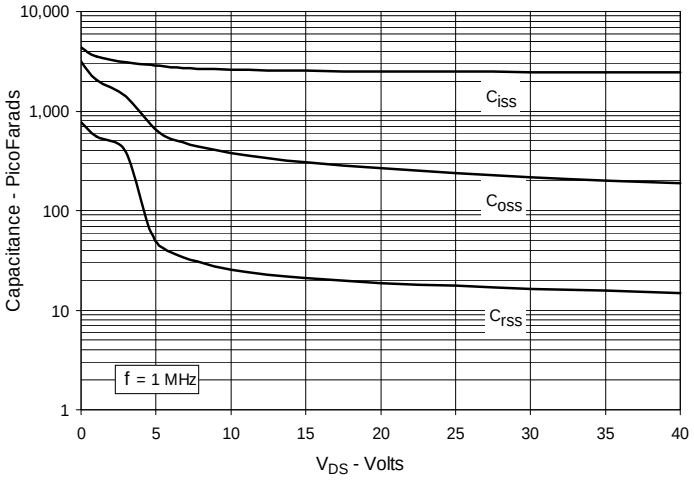


Fig. 11. Forward-Bias Safe Operating Area

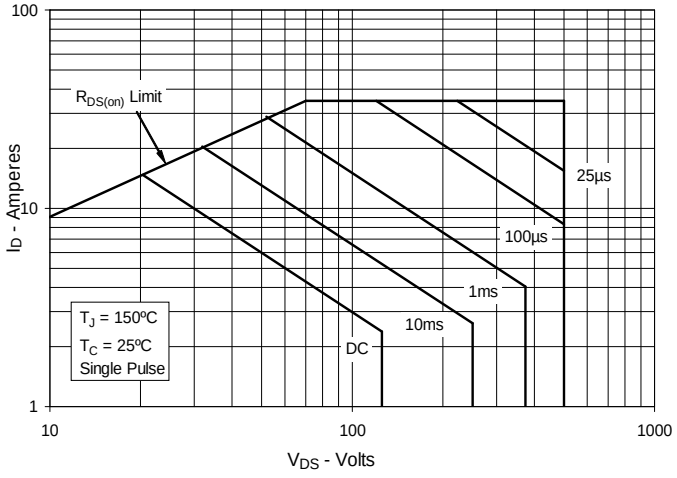
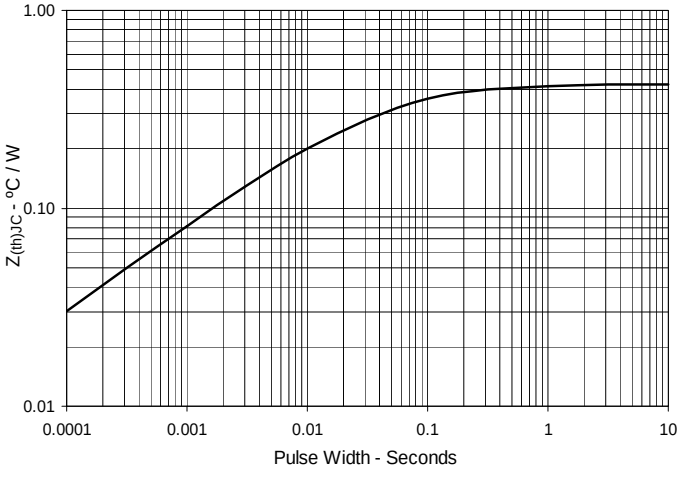


Fig. 12. Maximum Transient Thermal Impedance



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